# XPT IGBT

Single IGBT

Part number IXA20I1200PZ

### Features / Advantages:

- · Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10 µsec.
- very low gate charge
- low EMI
- square RBSOA @ 3x lc
- Thin wafer technology combined with the XPT design results in a competitive low VCE(sat)

#### **Applications:**

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

### Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

Terms Conditions of usage:

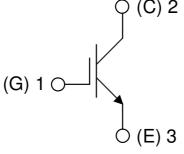
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

V<sub>CES</sub> 1200 V = | <sub>C25</sub> 38 A = V<sub>CE(sat)</sub> = 1.8V







## IXA20I1200PZ



# LIXYS

## IXA20I1200PZ

IGBT					I	Ratings	3	
Symbol	Definition		Conditions		min.	typ.	max.	Unit
V <sub>CES</sub>	collector emitter voltage			$T_{VJ} = 25^{\circ}C$			1200	V
$V_{GES}$	max. DC gate voltage						±20	V
$V_{\text{gem}}$	max. transient gate emitter voltage						±30	V
I <sub>C25</sub>	collector current			$T_c = 25^{\circ}C$			38	Α
I <sub>C80</sub>				$T_c = 80^{\circ}C$			22	Α
P <sub>tot</sub>	total power dissipation			$T_c = 25^{\circ}C$			165	W
V <sub>CE(sat)</sub>	collector emitter saturation voltage		$I_{c} = 15A; V_{GE} = 15V$	$T_{VJ} = 25^{\circ}C$		1.8	2.1	V
				T <sub>vJ</sub> = 125 °C		2.1		V
$V_{GE(th)}$	gate emitter threshold voltage		$I_{c} = 0.6 \text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}C$	5.4	5.9	6.5	V
I <sub>CES</sub>	collector emitter leakage current		$V_{\text{CE}} = V_{\text{CES}}; V_{\text{GE}} = 0 \text{ V}$	$T_{VJ} = 25^{\circ}C$			0.1	mA
				T <sub>vJ</sub> = 125 °C		0.1		mA
I <sub>GES</sub>	gate emitter leakage current		$V_{GE} = \pm 20 \text{ V}$				500	nA
Q <sub>G(on)</sub>	total gate charge		$V_{CE}$ = 600 V; $V_{GE}$ = 15 V; $I_{C}$ =	15 A		47		nC
t <sub>d(on)</sub>	turn-on delay time	)				48		ns
t,	current rise time		inductive load	T <sub>v.i</sub> = 125 °C		30		ns
t <sub>d(off)</sub>	turn-off delay time	L		$I_{VJ} = 125  {}^{\circ}\text{C}$		230		ns
t <sub>f</sub>	current fall time	ſ	$V_{CE} = 600 \text{ V}; I_{C} = 15 \text{ A}$			350		ns
<b>E</b> <sub>on</sub>	turn-on energy per pulse		$V_{\text{GE}} = \pm 15 \text{ V};  \text{R}_{\text{G}} = 56  \Omega$			1.6		mJ
<b>E</b> <sub>off</sub>	turn-off energy per pulse	J				1.7		mJ
RBSOA	reverse bias safe operating area	7	$V_{GE} = \pm 15 \text{ V}; \text{ R}_{G} = 56 \Omega$	T <sub>vJ</sub> = 125 °C				
I <sub>CM</sub>		ſ	$V_{CEmax} = 1200 V$				45	Α
SCSOA	short circuit safe operating area	٦	$V_{CEmax} = 1200 V$					
t <sub>sc</sub>	short circuit duration	}	$V_{CE} = 900 \text{ V}; V_{GE} = \pm 15 \text{ V}$	T <sub>vJ</sub> = 125 °C			10	μs
l <sub>sc</sub>	short circuit current	J	$R_{g}$ = 56 $\Omega$ ; non-repetitive			60		Α
$\mathbf{R}_{thJC}$	thermal resistance junction to case						0.76	K/W
$\mathbf{R}_{thCH}$	thermal resistance case to heatsink					0.25		K/W

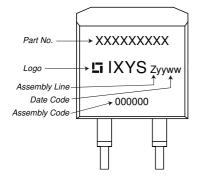
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## IXA20I1200PZ

Package TO-263 (D2Pak-HV)			F	Ratings			
Symbol	Definition 0	Conditions		min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current P	er terminal				35	Α
T <sub>vJ</sub>	virtual junction temperature			-40		150	°C
T <sub>op</sub>	operation temperature			-40		125	°C
T <sub>stg</sub>	storage temperature			-40		150	°C
Weight					1.5		g
F <sub>c</sub>	mounting force with clip			20		60	Ν
d <sub>Spp/App</sub>	creepage distance on surface   striking distar	and through air	terminal to terminal	4.2			mm
d <sub>Spb/Apb</sub>	creepage distance on surface   surfing distan	stance through an	terminal to backside	4.7			mm

### **Product Marking**



#### Part description

|--|

- X = XPT IGBT
- A = Gen 1 / std 20 = Current Rating [A] I = Single IGBT
- 1200 = Reverse Voltage [V] PZ = TO-263AB (D2Pak) (2HV)

[	Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	IXA20I1200PZ	IXA20I1200PZ	Tape & Reel	800	518533

Similar Part	Package	Voltage class
IXA20I1200PZ	TO-220AB (3)	1200
IXA20IF1200HB	TO-247AD (3)	1200

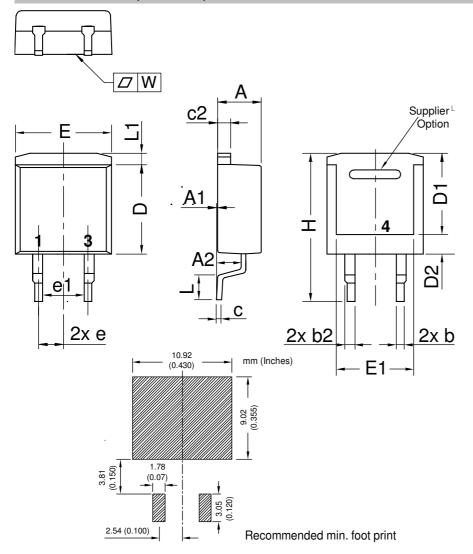
Equiv	alent Circuits for Simulation	* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
	)-[	IGBT	
V <sub>0 max</sub>	threshold voltage	1.1	V
$\mathbf{R}_{0 \max}$	slope resistance *	86	mΩ

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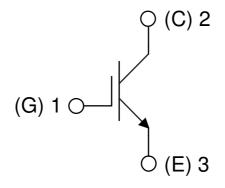
## IXA20I1200PZ

### Outlines TO-263 (D2Pak-HV)



Dim.	Millir	neter	Inc	hes	
Din.	min	max	min	max	
Α	4.06	4.83	0.160	0.190	
A1	typ.	0.10	typ. 0.004		
A2	2.	41	0.095		
b	0.51	0.99	0.020	0.039	
b2	1.14	1.40	0.045	0.055	
С	0.40	0.74	0.016	0.029	
c2	1.14	1.40	0.045	0.055	
D	8.38	9.40	0.330	0.370	
D1	8.00	8.89	0.315	0.350	
D2	2.3		0.091		
Е	9.65	10.41	0.380	0.410	
E1	6.22	8.50	0.245	0.335	
е	2,54 BSC		0,100 BSC		
e1	4.28		0.169		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	1.02	1.68	0.040	0.066	
W	typ. 0.02	0.040	typ. 0.0008	0.002	

All dimensions conform with and/or within JEDEC standard.



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600

500

400

300

200

100

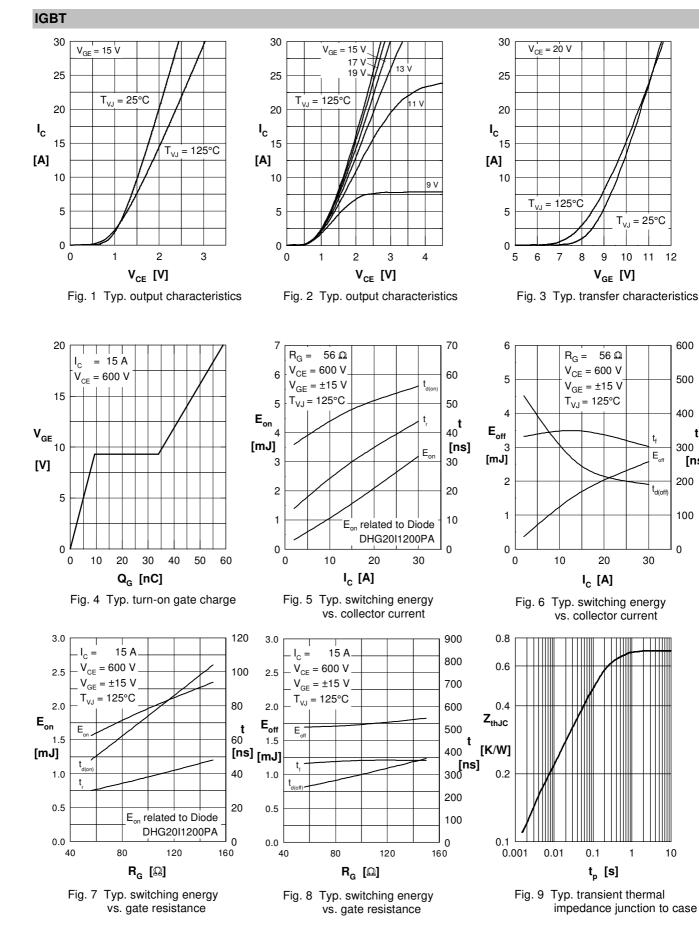
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